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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF

YUUICHI HIRANO ET AL.

: EXAMINER: TRAN, T.

SERIAL NO: 09/802,886

: GROUP ART UNIT: 2811

FILED: MARCH 12, 2001
FOR: SEMICONDUCTOR DEVICE AND
METHOD OF MANUFACTURING
THE SAME

RESPONSE

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action of November 8, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend independent Claim 1 to read as follows:¹

- Sub C*
- B*
1. (Twice Amended) A semiconductor device comprising:
an SOI substrate having a structure in which a semiconductor substrate, an insulating layer and a semiconductor layer are layered in this order;
a partial-isolation insulating film formed in a main surface of said semiconductor layer;

¹A marked-up copy of the amendments is attached hereto.